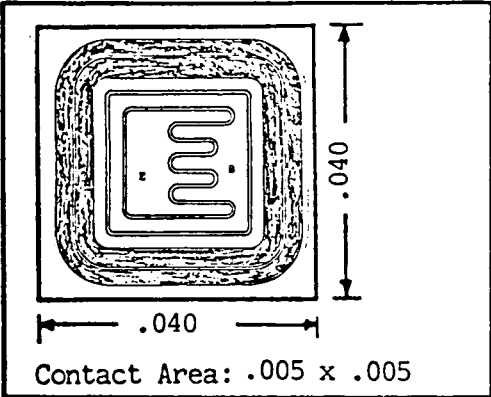


X00220

STX625 CHIP
HIGH VOLTAGE PNP TRANSISTOR CHIP



CONTACT METALLIZATION
 Base/Emitter: > 30,000 Å Aluminum
 Collector: > 2,000 Å Evaporated Gold

ASSEMBLY RECOMMENDATIONS

1. Eutectic Die Attach.
2. Ultrasonically Attach 2 MIL Aluminum Wire To Base/Emitter Contacts.

PARAMETER	TEST CONDITIONS	TYPE	MIN.	MAX.	UNIT
BV _{CEO}	I _C = 1 mA (pulsed)		450		Vdc
BV _{CBO}	I _C = 100 uA		500		Vdc
BV _{CER}	I _C = 100 uA, R _{BE} = 5 K Ohm		500		Vdc
BV _{EBO}	I _E = 20 uA				Vdc
I _{EBO}	V _{EB} = 4 V			250	uA
I _{CBO}	V _{CB} = 500 V			500	nA
h _{FE}	V _{CE} = 10 V, I _C = 1 mA		20	200	
h _{FE}	V _{CE} = 10 V, I _C = 25 mA		40	250	
h _{FE}	V _{CE} = 15 V, I _C = 100 mA		20	200	
V _{BE(SAT)}	I _C = 25 mA, I _B = 2.5 mA			1.0	Vdc
V _{CE(SAT)}	I _C = 25 mA, I _B = 2.5 mA			3.0	Vdc
C _{OB}	V _{CB} = 15 V			20	pf
f _T	V _{CE} = 20 V, I _C = 10 mA f = 5 MHz		20		MHz

Electrical characteristics measured at lot acceptance testing in a TO-5 package. Specifications subject to change without notice.

SSDI SOLID STATE DEVICES, INC.

P.O. Box 577, La Mirada, California, 90637-0577 TWX 910-583-4807
 14830 Valley View Avenue, La Mirada, California, 90638 (213) 921-9660